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PROCESS FOR IMPROVING THE ETCH STABILITY
OF ULTRA-THIN PHOTORESIST

ABSTRACT OF THE DISCLOSURE

An integrated circuit fabrication process is disclosed herein. The process includes exposing a photoresist layer to a plasma, and transforming the top surface and the side surfaces of the photoresist layer to form a hardened surface. The process further includes etching the substrate in accordance with the

5 transformed feature, wherein an etch stability of the feature is increased by the hardened surface. The photoresist layer is provided at a thickness less than 0.25 μm , for use in deep ultraviolet lithography, or for use in extreme ultraviolet lithography.

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